NSN 5961-01-354-4112

Diode Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-354-4112 **Inclosure Material:** Glass **Overall Length:** Between 0.140 inches and 0.195 inches **Terminal Length:** 1.000 inches **Overall Diameter:** Between 0.135 inches and 0.185 inches **Function For Which Designed:** Transient suppressor **Mounting Method: Terminal Features Provided:** Quality assurance level txv **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 190.0 breakdown voltage, dc and 152.0 working peak reverse voltage **Current Rating Per Characteristic:** 5.00 milliamperes collector current, dc horsepower metric and 5.50 amperes source cutoff current pascal **Power Rating Per Characteristic:** 3.0 watts small-signal input power, common-collector major **Maximum Operating Tempurature Per Measurement Point:** 175.0 degrees celsius ambient air **Test Data Document:** 81349-mil-prf-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.). **Terminal Type And Quantity:** 2 uninsulated wire lead **Specification Data:** 81349-mil-prf-19500/516 government specification Shelf Life: N/a **Unit Of Measure: Demilitarization:**

Fiig: A110a0

No

Mil-std (military Standard):

Mil-prf-19500 spec.